

# Chapter 5

## Elements of Physical Design

Jin-Fu Li

Advanced Reliable Systems (ARES) Lab.  
Department of Electrical Engineering  
National Central University  
Jhongli, Taiwan

# Outline

- Basic Concepts
- Layout of Basic Structures
- Cell Concepts
- MOS Sizing
- Physical Design of Logic Gates
- Design Hierarchies

# Basic Concepts

- *Physical design*
  - The actual process of creating circuits on silicon
  - During this phase, schematic diagrams are carefully translated into sets of geometric patterns that are used to define the on-chip physical structures
- Every layer in the CMOS fabrication sequence is defined by a distinct pattern
- The process of physical design is performed using a computer tool called a **layout editor**
  - A graphics program that allows the designer to specify the shape, dimensions, and placement
- Complexity issues are attacked by first designing simple gates and storing their descriptive files in a **library** subdirectory or folder

# Basic Concepts

- The gates constitute **cells** in the library
- Library cells are used as building blocks by creating copies of the basic cells to construct a larger more complex circuit
  - This process is called *instantiate* of the cell
  - A copy of a cell is called an *instance*
- Much of the designer's work is directed toward the goal of obtaining a fast circuit in the minimum amount of area
  - Small changes in the shapes or area of a polygon will affect the resulting electrical characteristics of the circuit

# CAD Toolsets

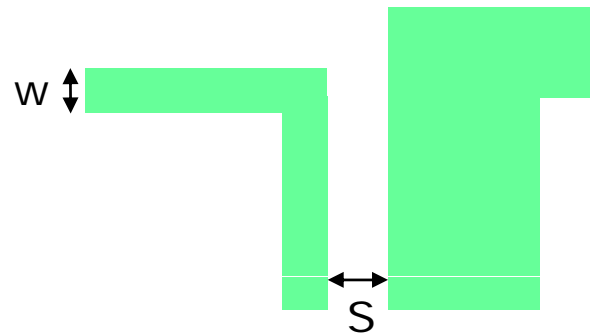
- Physical design is based on the use of CAD tools
  - Simplify the procedure and aid in the verification process
- Physical design toolsets
  - Layout editor
  - Extraction routine
  - Layout versus schematic (LVS)
  - Design rule checker (DRC)
  - Place and route routine
  - Electrical rule checker (ERC)

# Layout of Basic Structures

- The masking sequence of the P-substrate technology was established as
  - Start with P-type substrate
  - nWell
  - Active
  - Poly
  - pSelect
  - nSelect
  - Active Contact
  - Poly contact
  - Metal1
  - Via
  - Metal2
  - ...

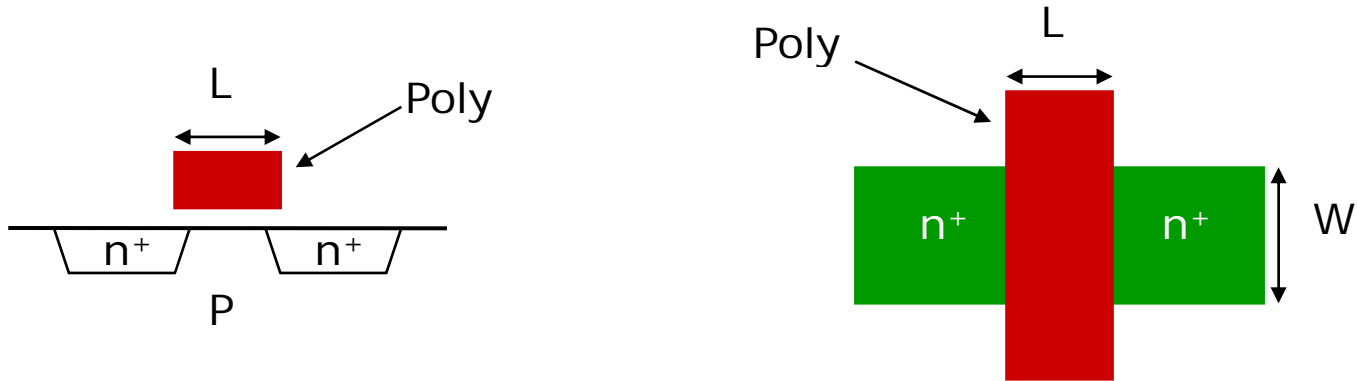
# Layout of Basic Structures

- It is worth remembering that the features on every level have design rule specifications for the minimum width  $w$  of a line, and a minimum edge-to-edge spacing  $s$  between adjacent polygons
- For example,

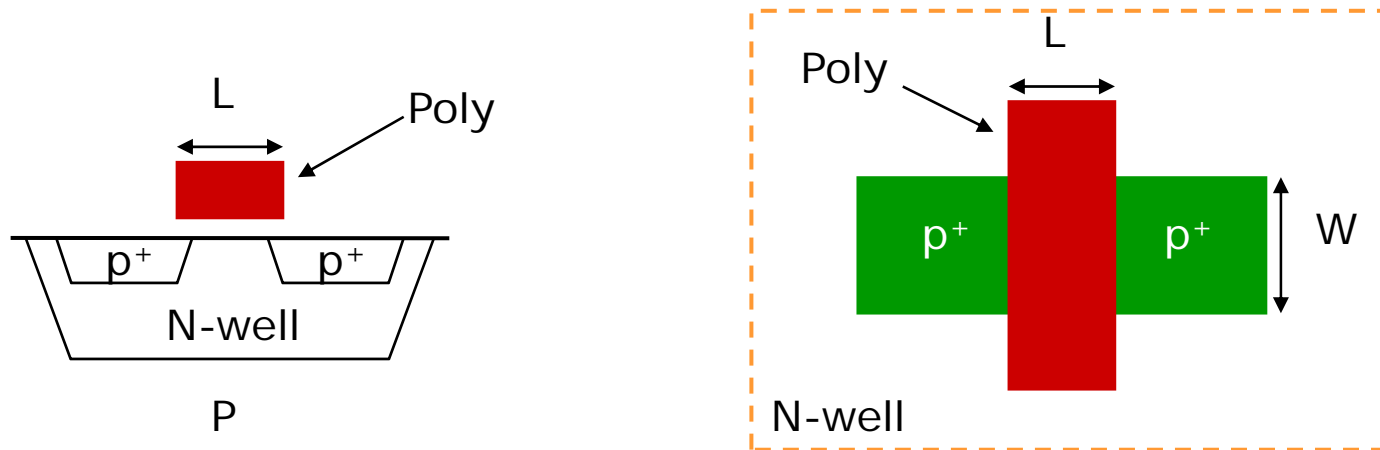


# Layouts of PMOS & NMOS

## □ NMOS



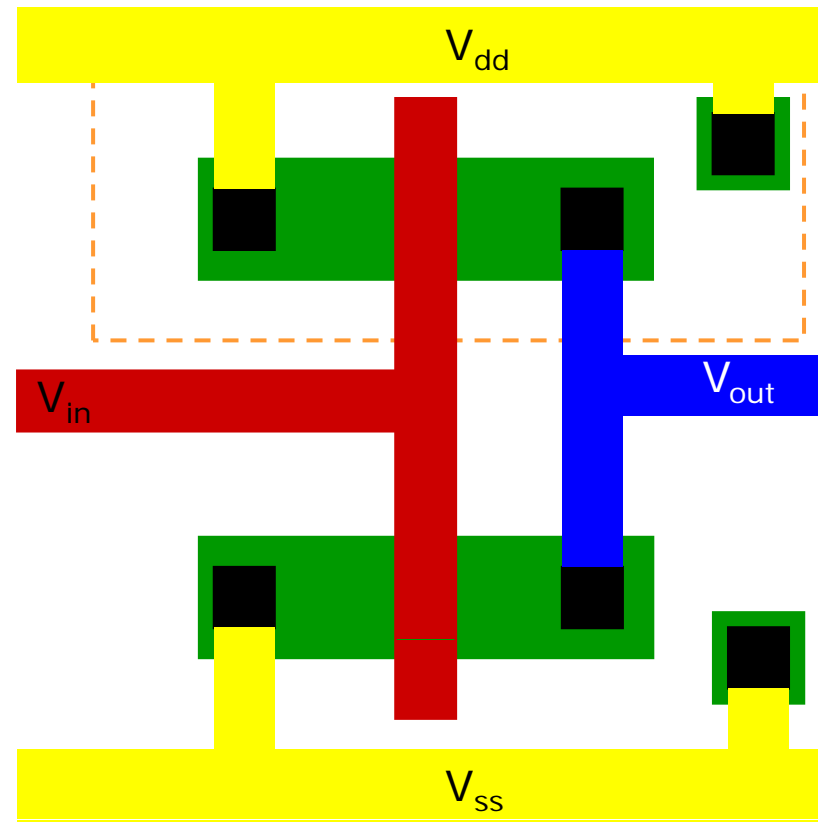
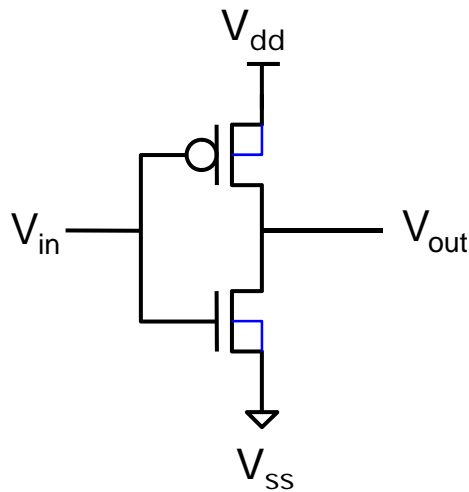
## □ PMOS



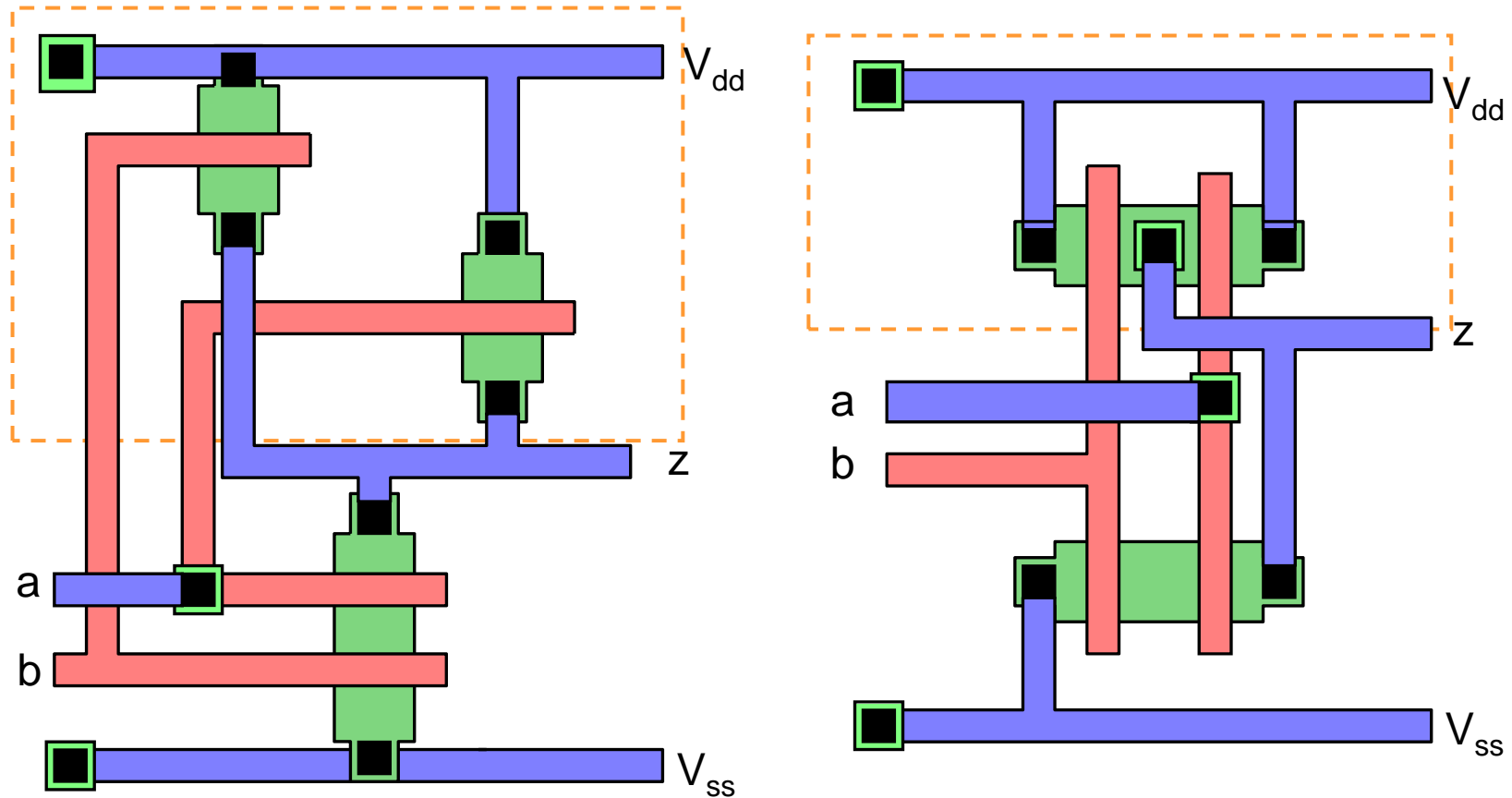


# The Layout of a CMOS Inverter

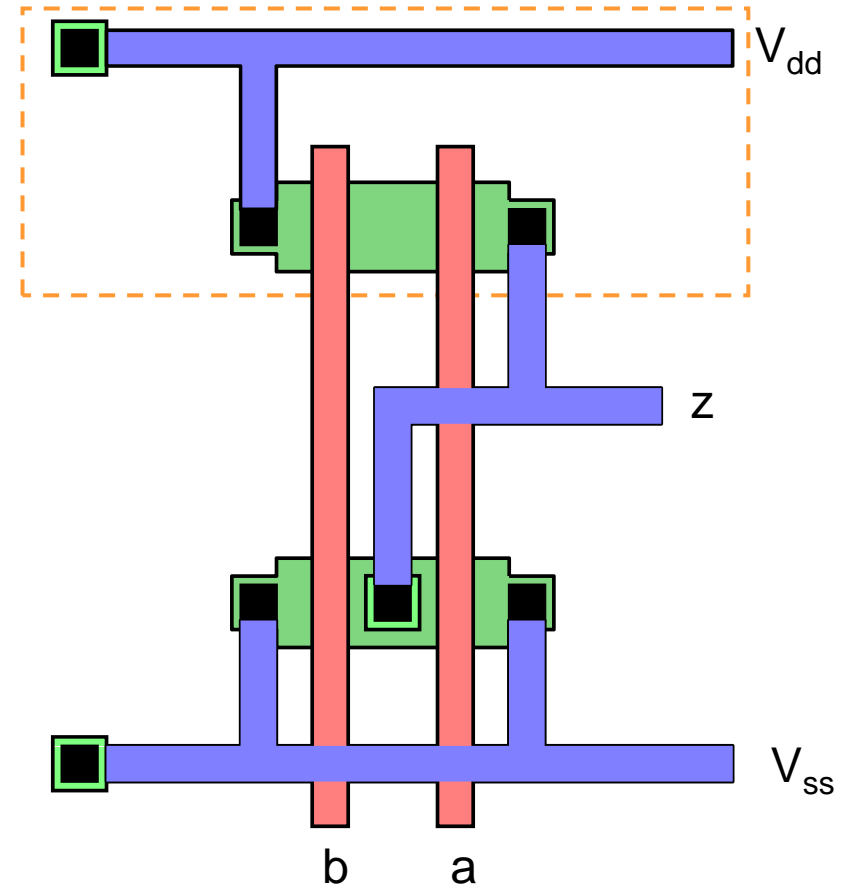
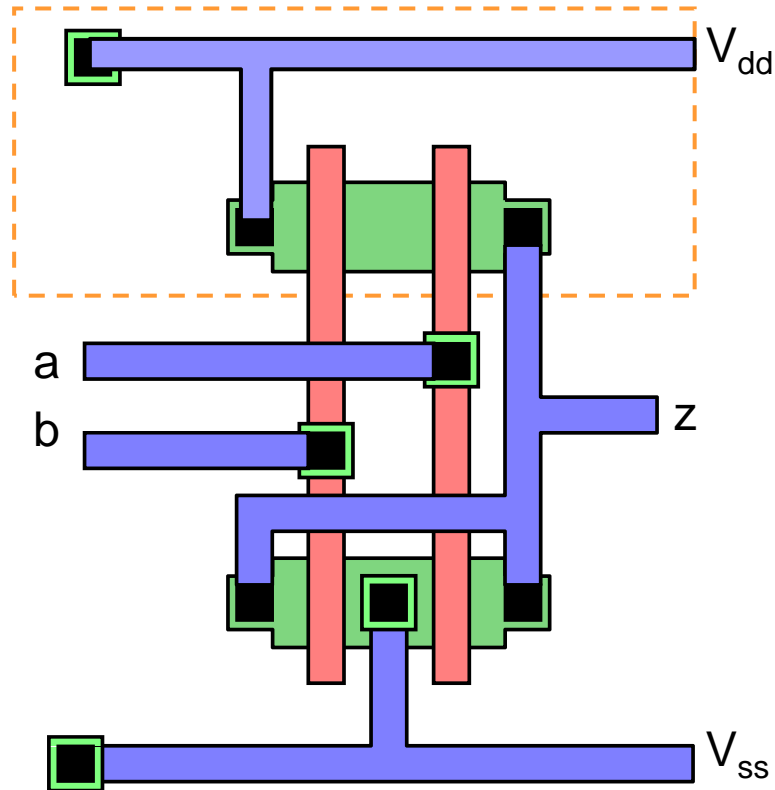
- A transistor-level CMOS inverter & the corresponding layout



# Layouts of a 2-Input NAND Gate

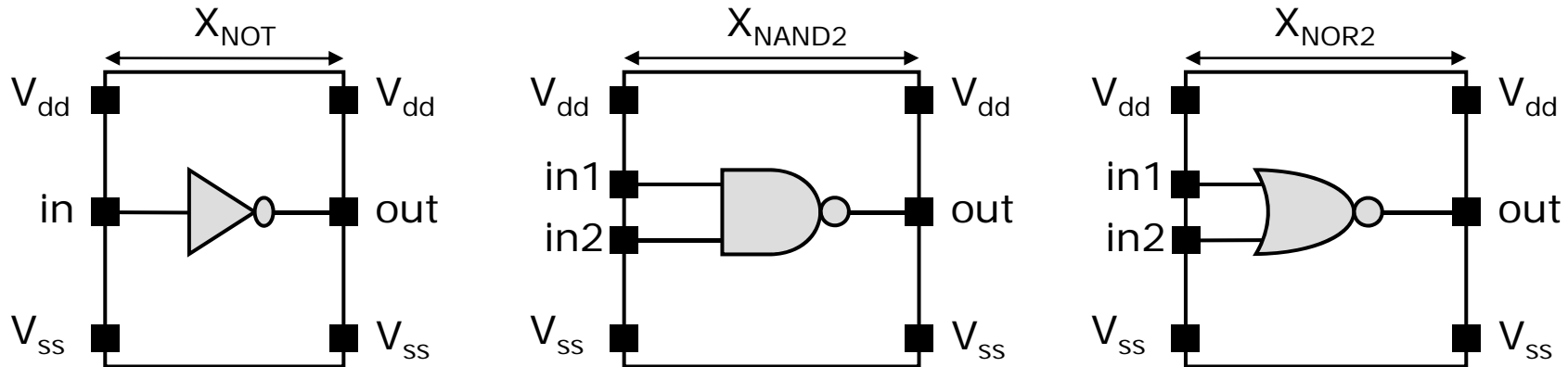


# Layouts of a 2-Input NOR Gate



# Cell Concepts

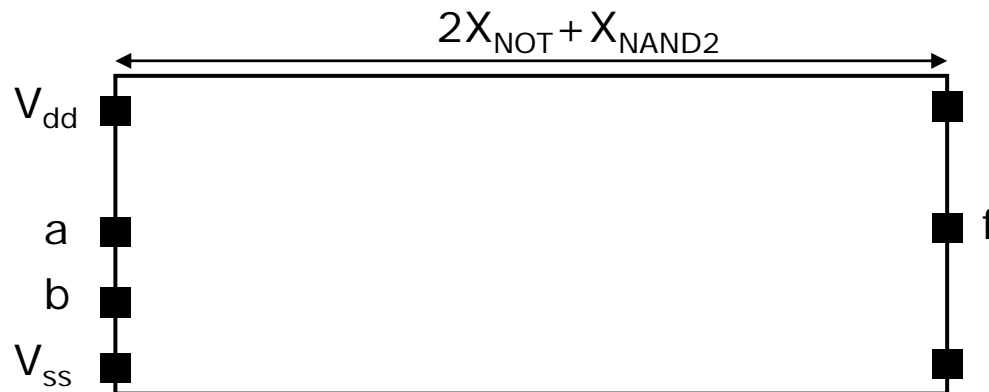
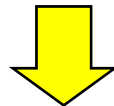
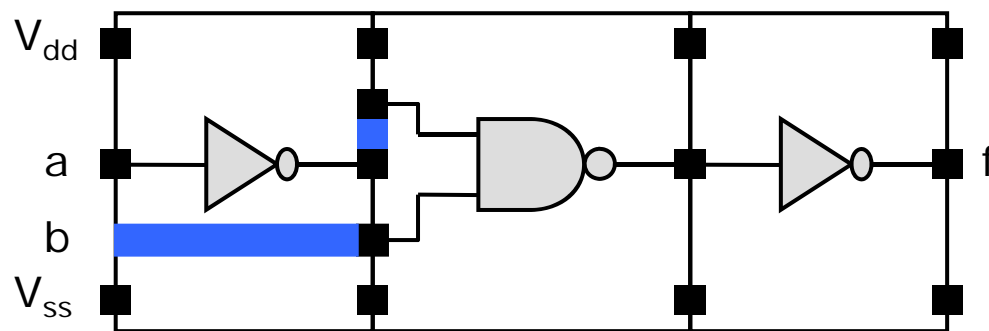
- The basic building blocks in physical design are called **cells**
- Logic gates as basic cells



- Note that power supply ports for  $V_{dd}$  and  $V_{ss}$  are chosen to be at the same locations for every cell
- The width of each cell depends on the transistor sizes and wiring used at the physical level

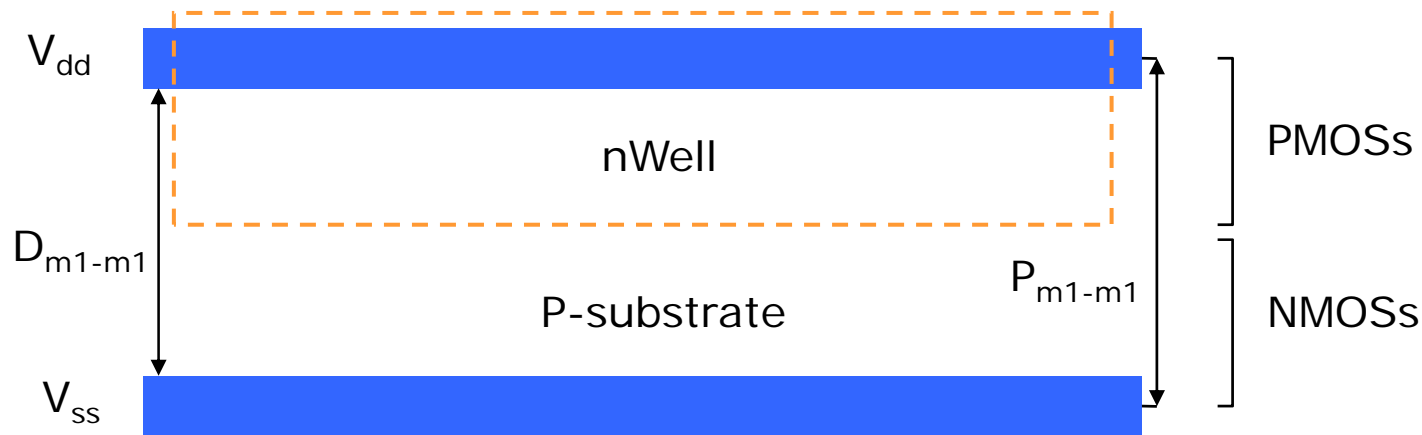
# Cell Creation Using Primitive Cells

- Create a new cell providing the function
  - $f = a'b$



# Layout of Cells

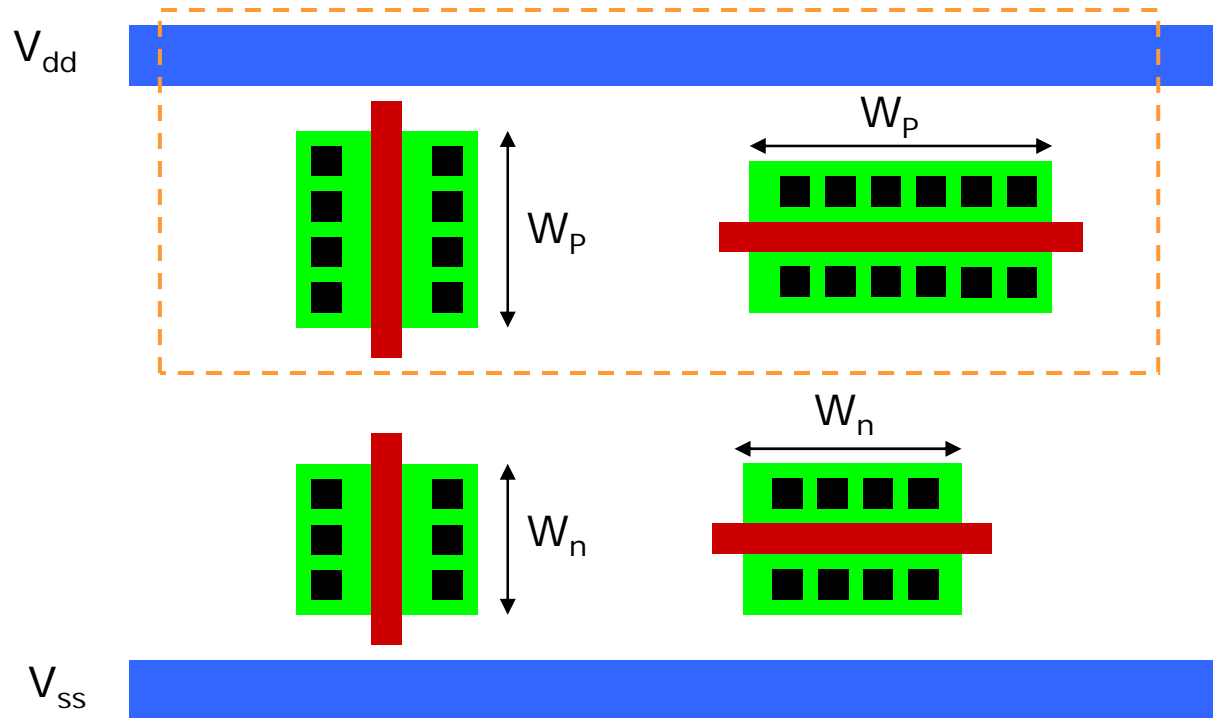
- $V_{dd}$  &  $V_{ss}$  power supply lines



- $D_{m1-m1}$ : edge-to-edge distance between  $V_{dd}$  and  $V_{ss}$
- $P_{m1-m1}$ : distance between the middle of the  $V_{dd}$  and  $V_{ss}$  lines
- $P_{m1-m1} = D_{m1-m1} + W_{dd}$ , where  $W_{dd}$  is the width of the power supply lines

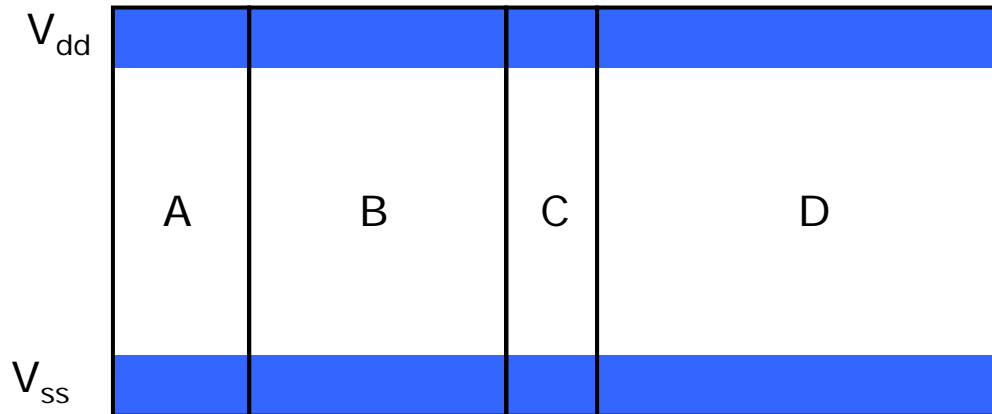
# Layout of Cells

## □ Layout styles of transistors

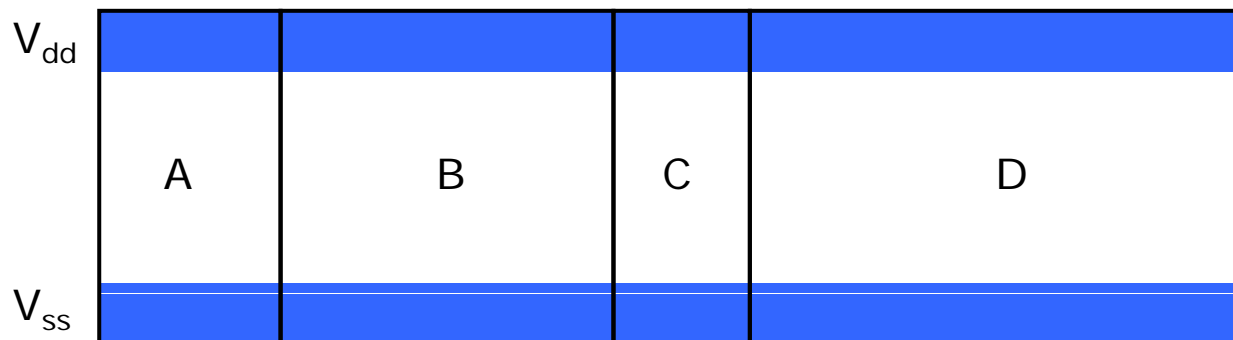


# Effect of Layout Shapes

- Larger spacing between  $V_{dd}$  and  $V_{ss}$



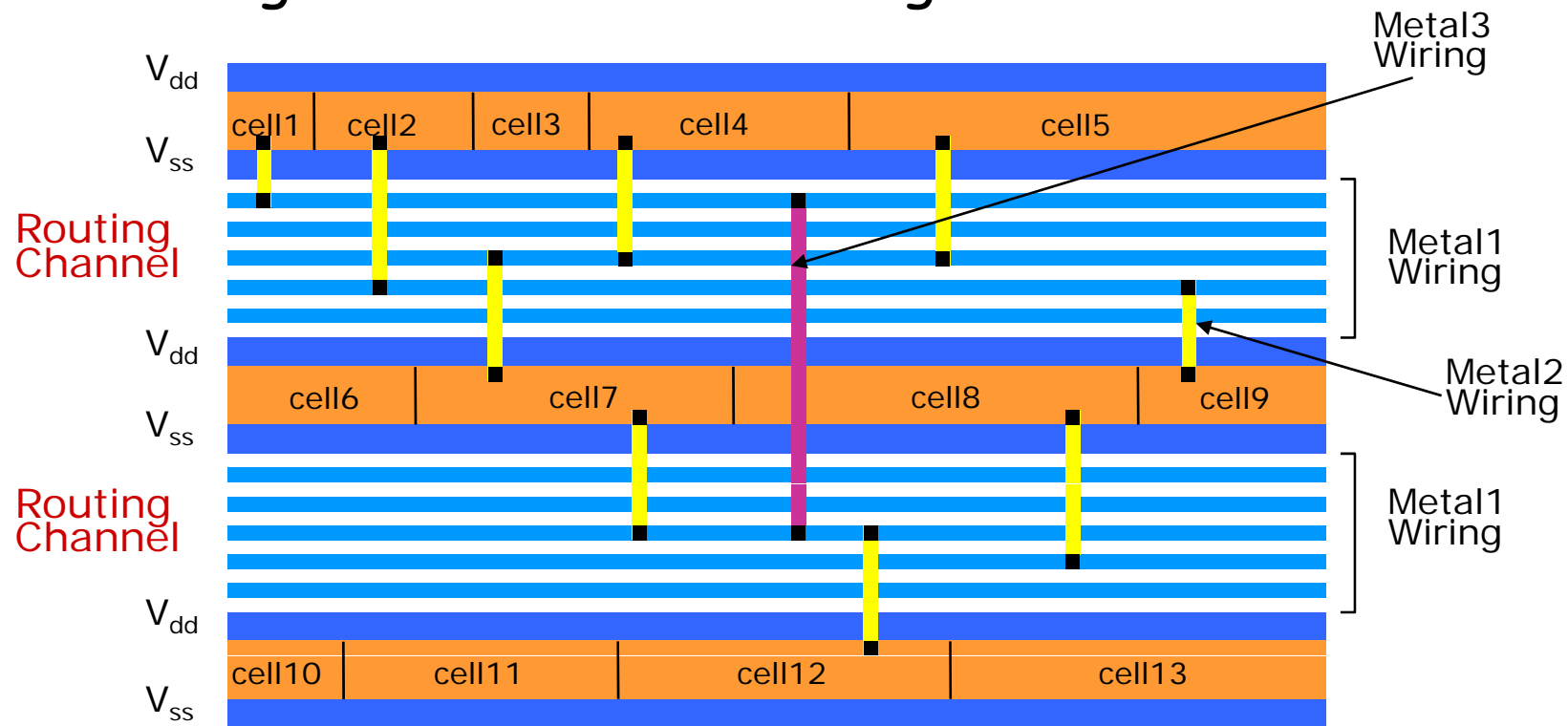
- Smaller spacing between  $V_{dd}$  and  $V_{ss}$





# Routing Channels

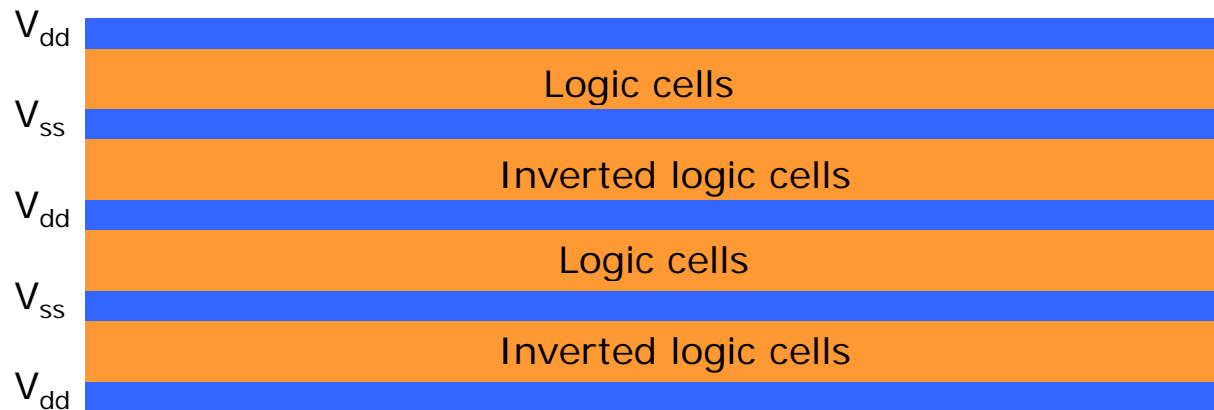
- Interconnection routing considerations are very important considerations for the  $V_{ss}$ - $V_{dd}$  spacing
  - In complex digital systems, the wiring is often more complicated than designing the transistor arrays
  - The general idea for routing



# High-Density Techniques

- Alternate  $V_{dd}$  and  $V_{ss}$  power lines and share them with cells above and below

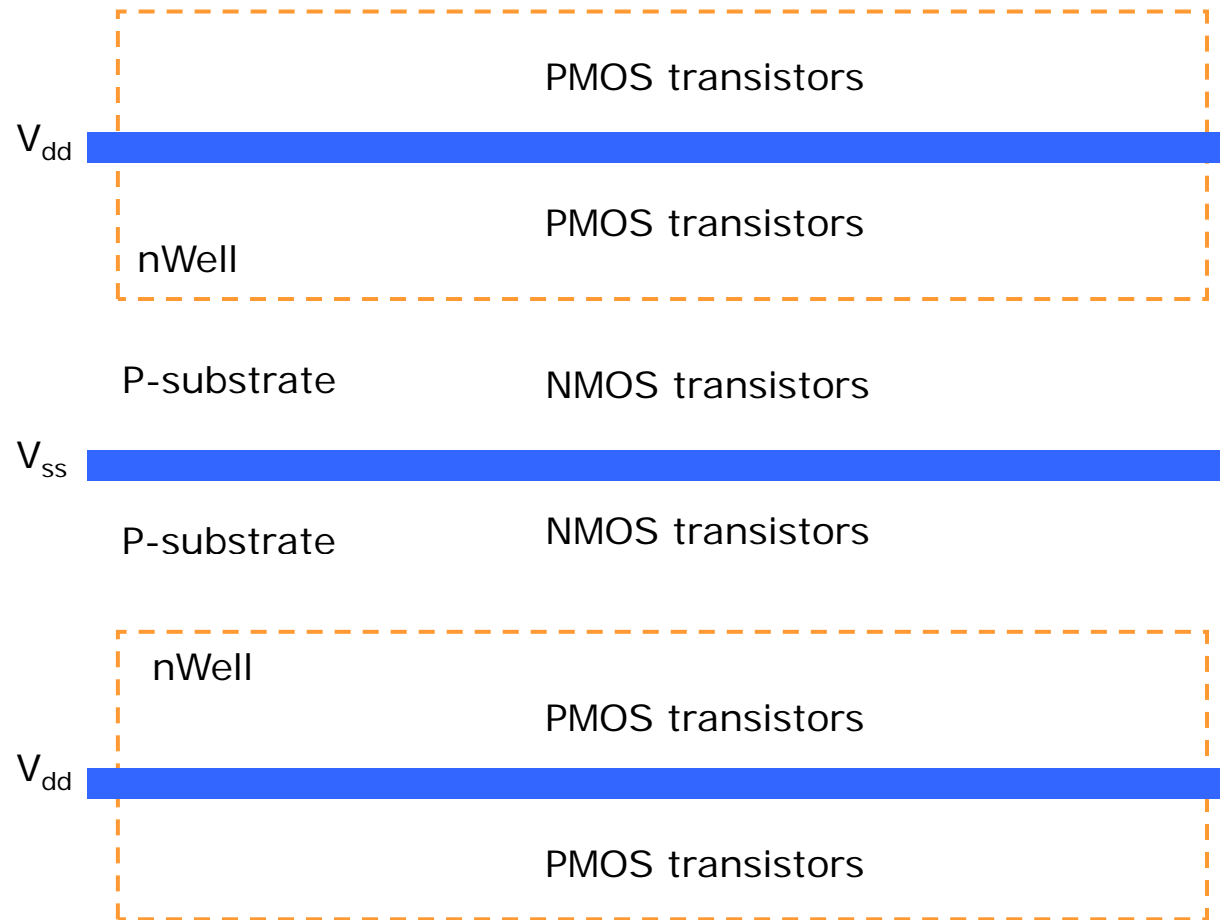
- For example,



- Since no space is automatically reserved for routing, this scheme allows for high-density of placement of cells
- The main drawback is that the connection between rows must be accomplished by using Metal2 or higher

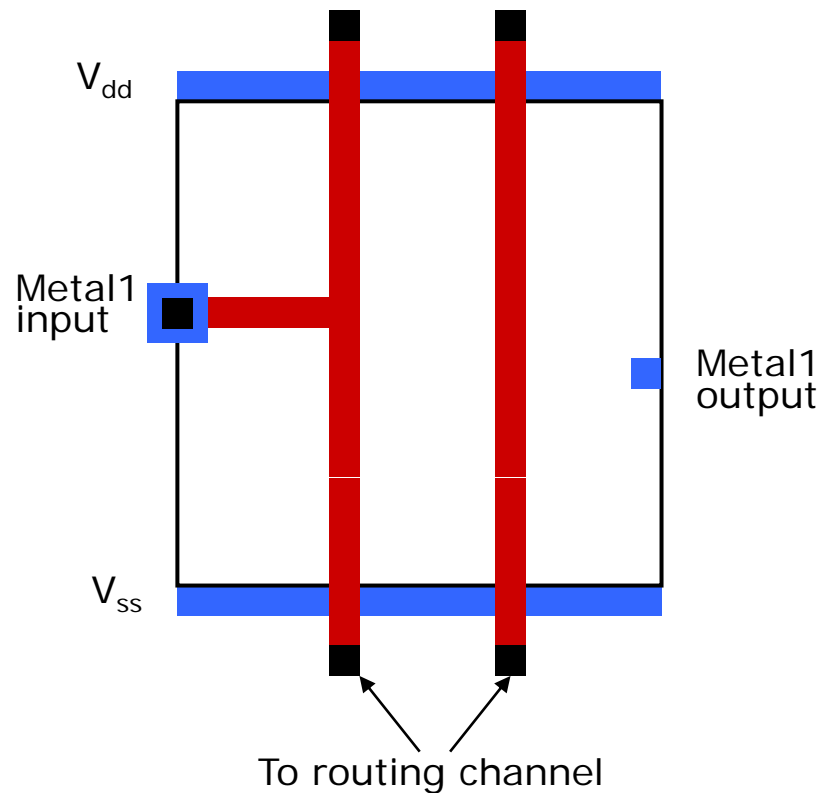
# High-Density Techniques

## □ MOS transistor placement



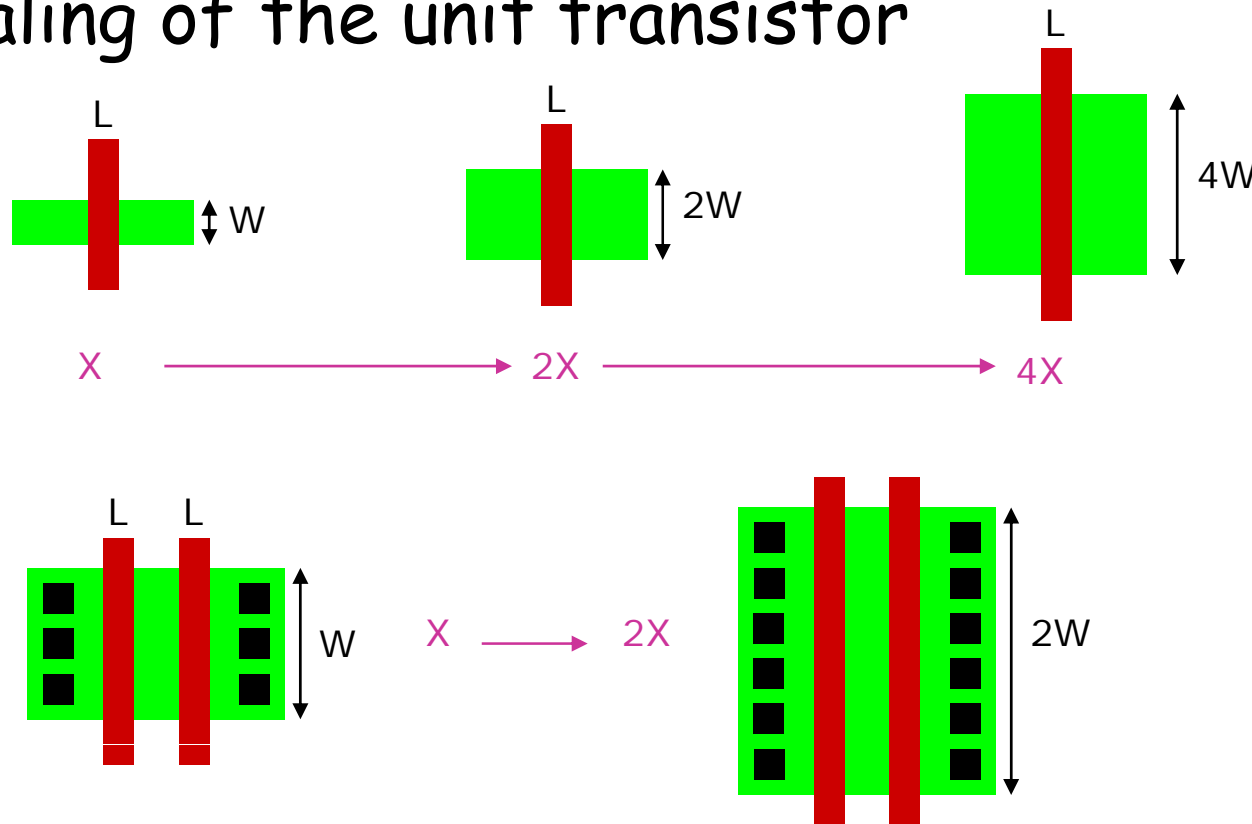
# Port Placement

- An example of the port placement in a cell

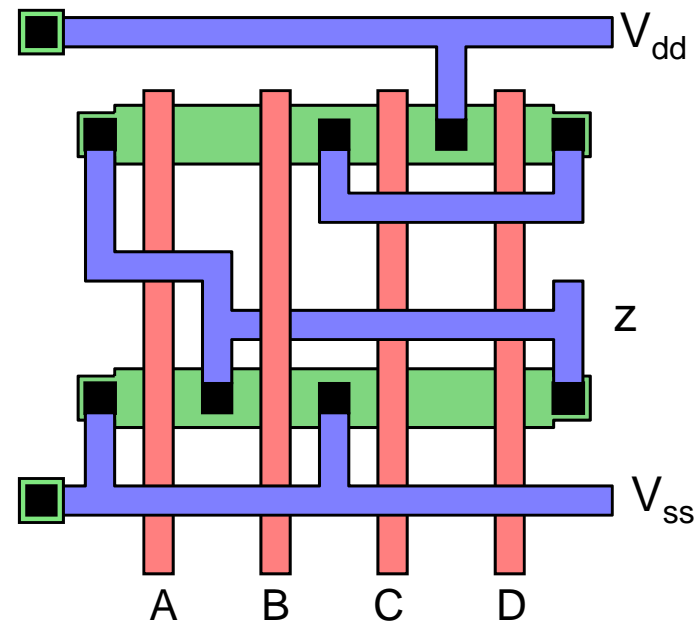
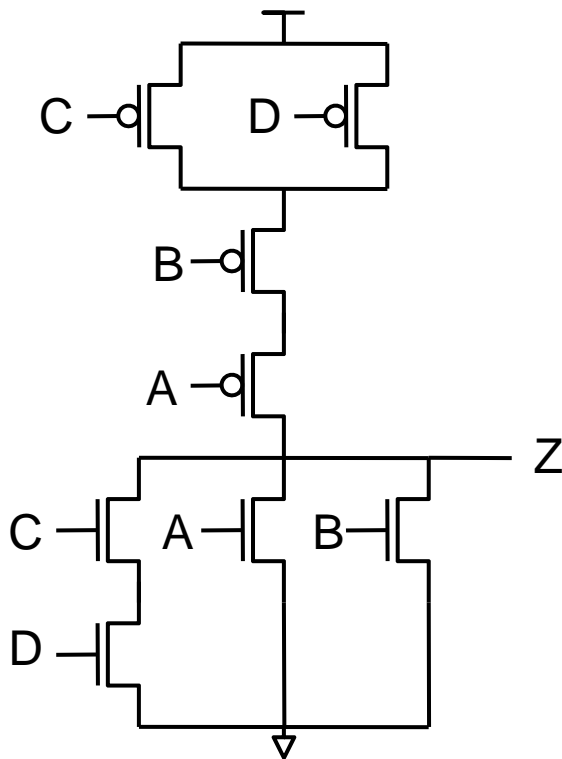


# MOS Sizing in Physical Design

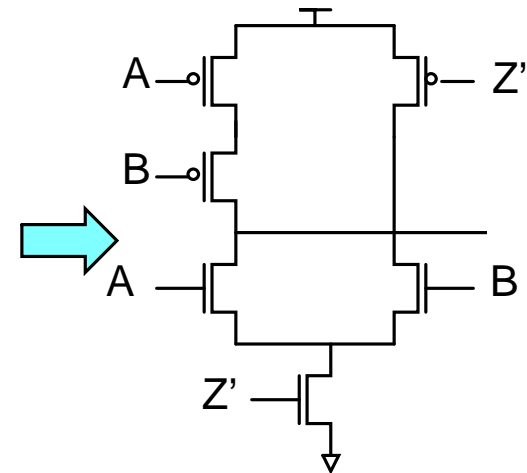
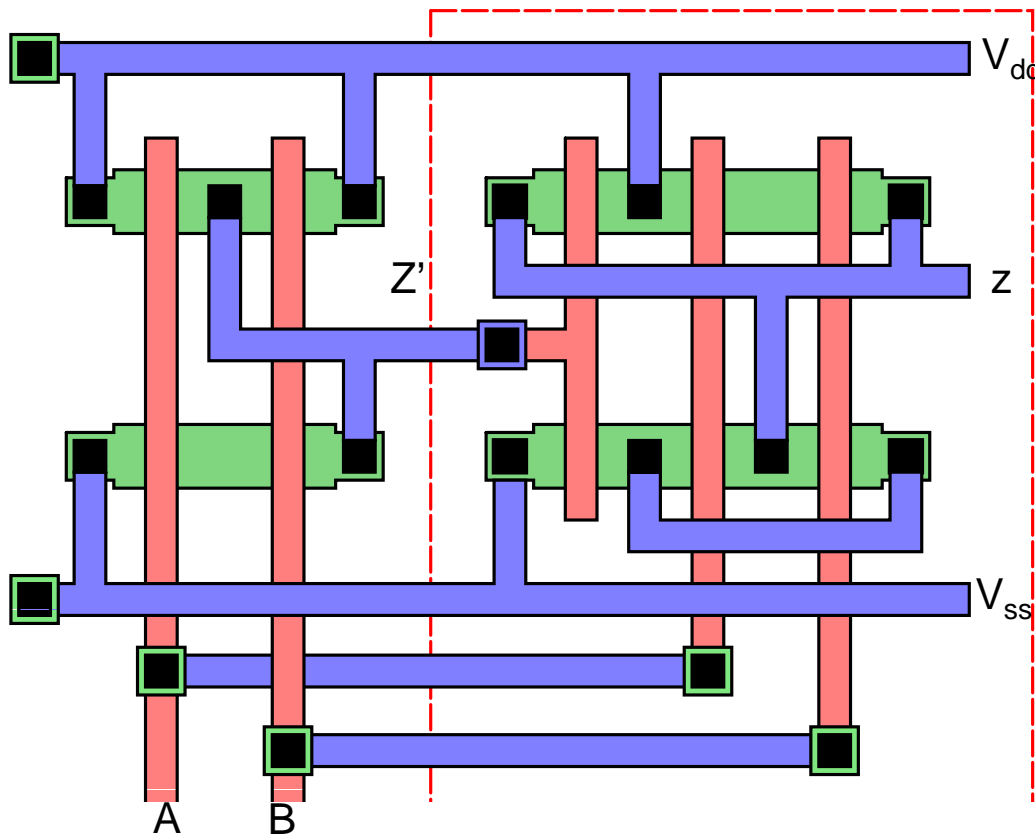
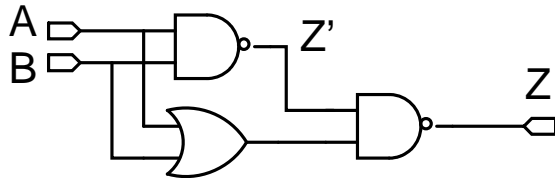
- A minimum-size MOS transistor is the smallest transistor that can be created using the design rule set
- Scaling of the unit transistor



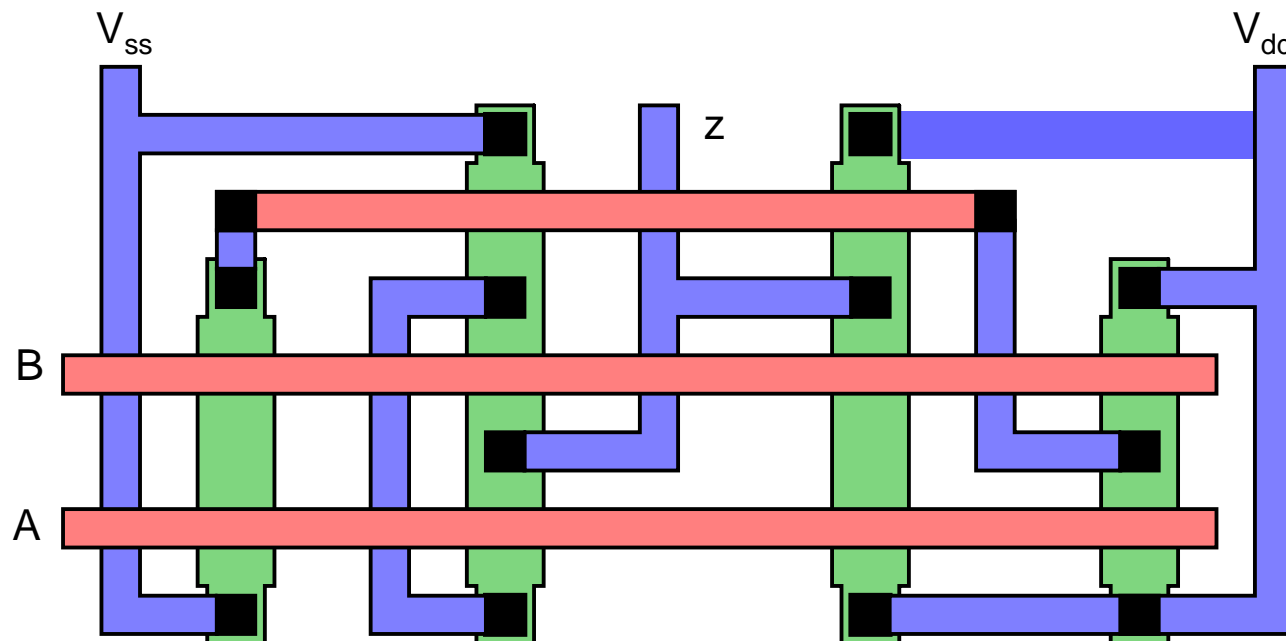
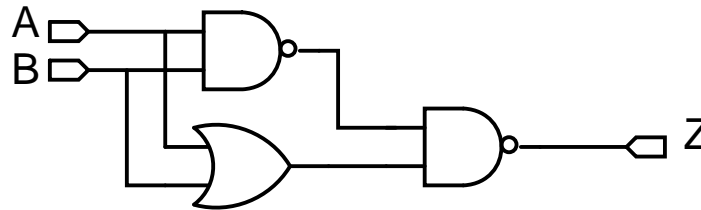
# Physical Designs of Complex Gates



# Physical Design of XNOR Gate (1)

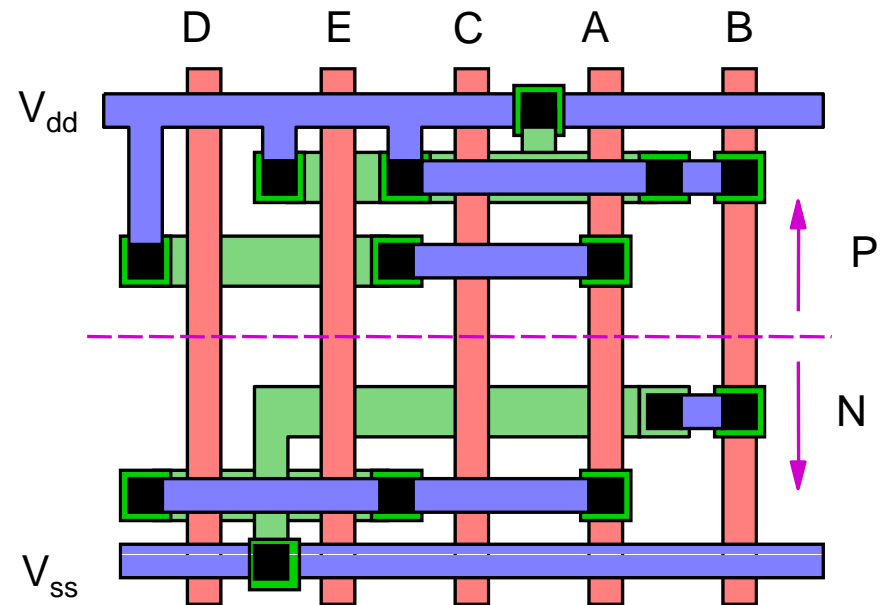
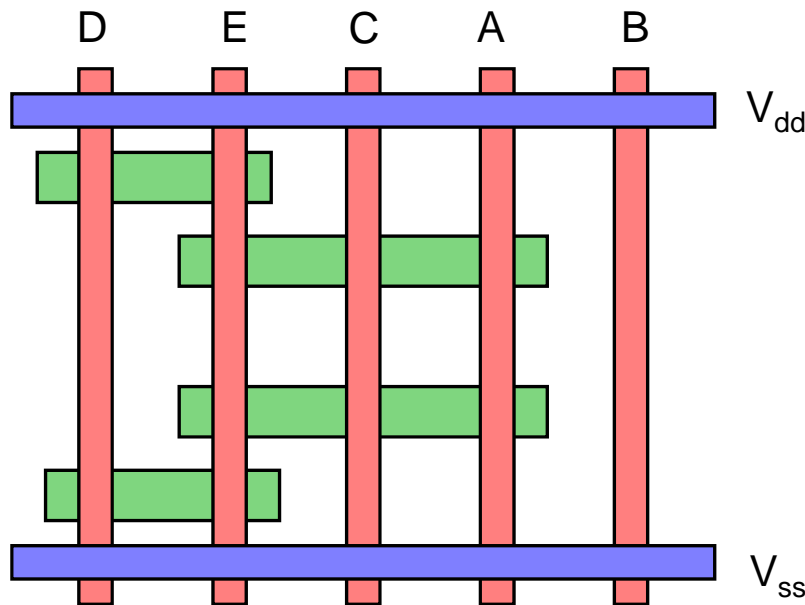
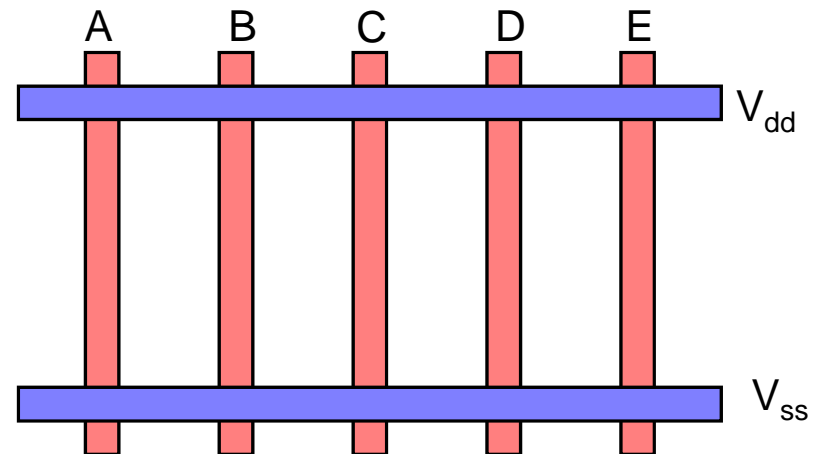
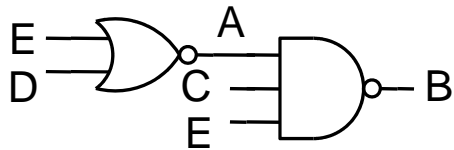


# Physical Design of XNOR Gate (2)

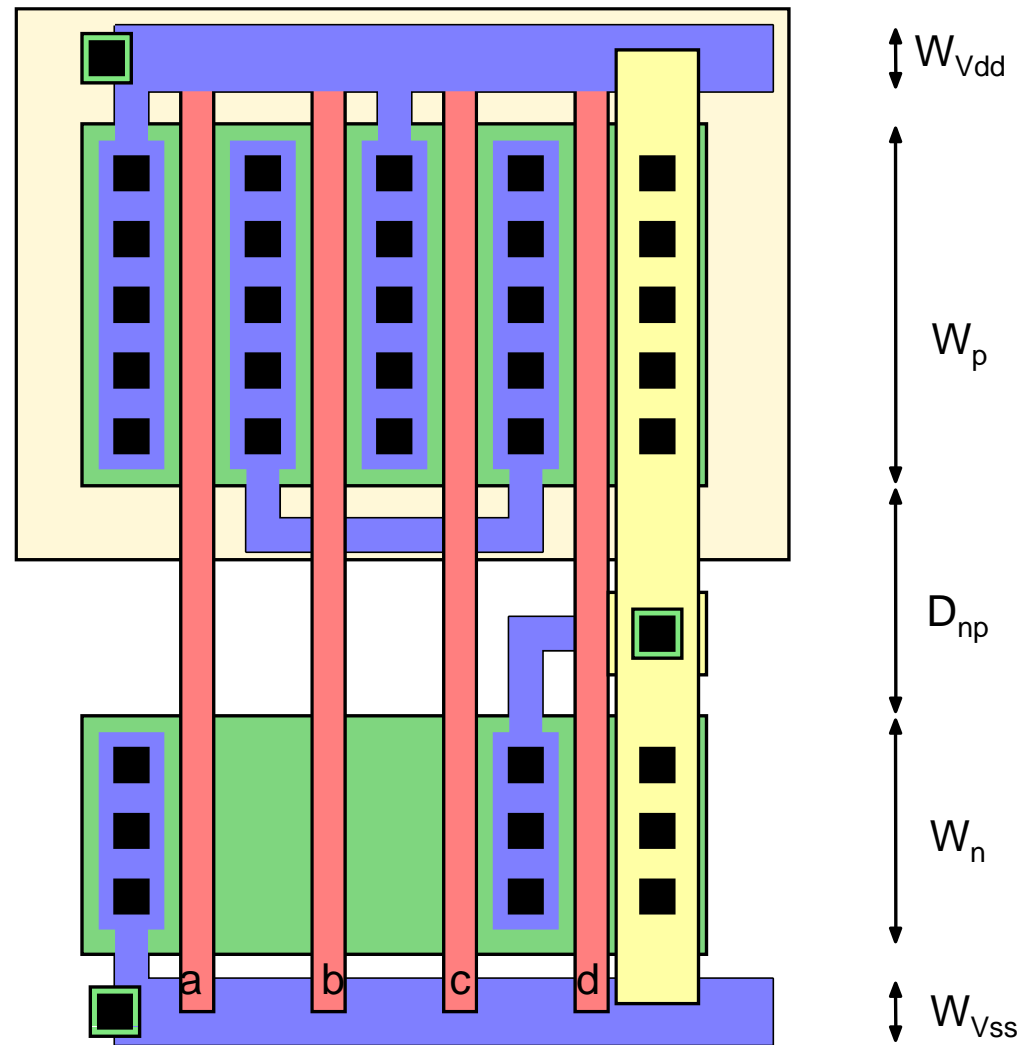




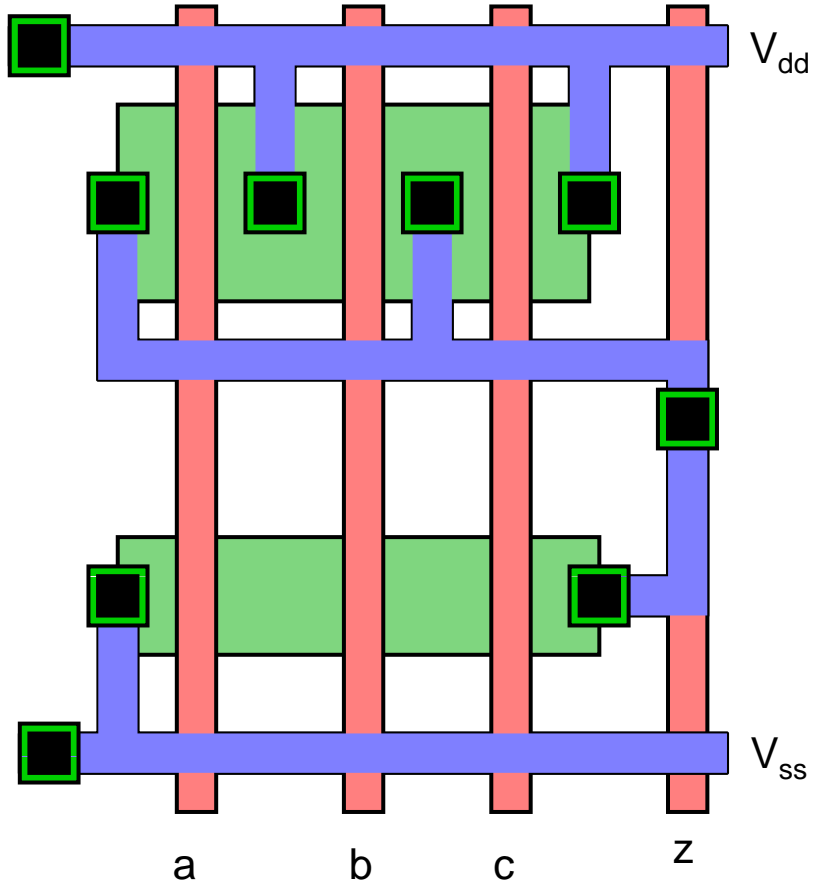
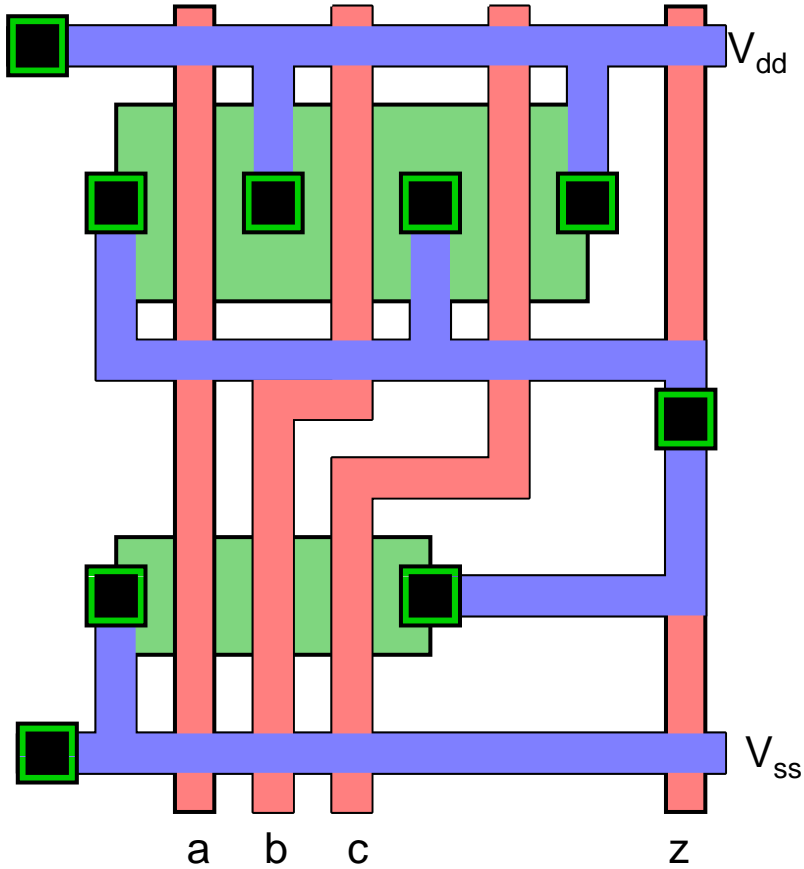
# Automation of Physical Design



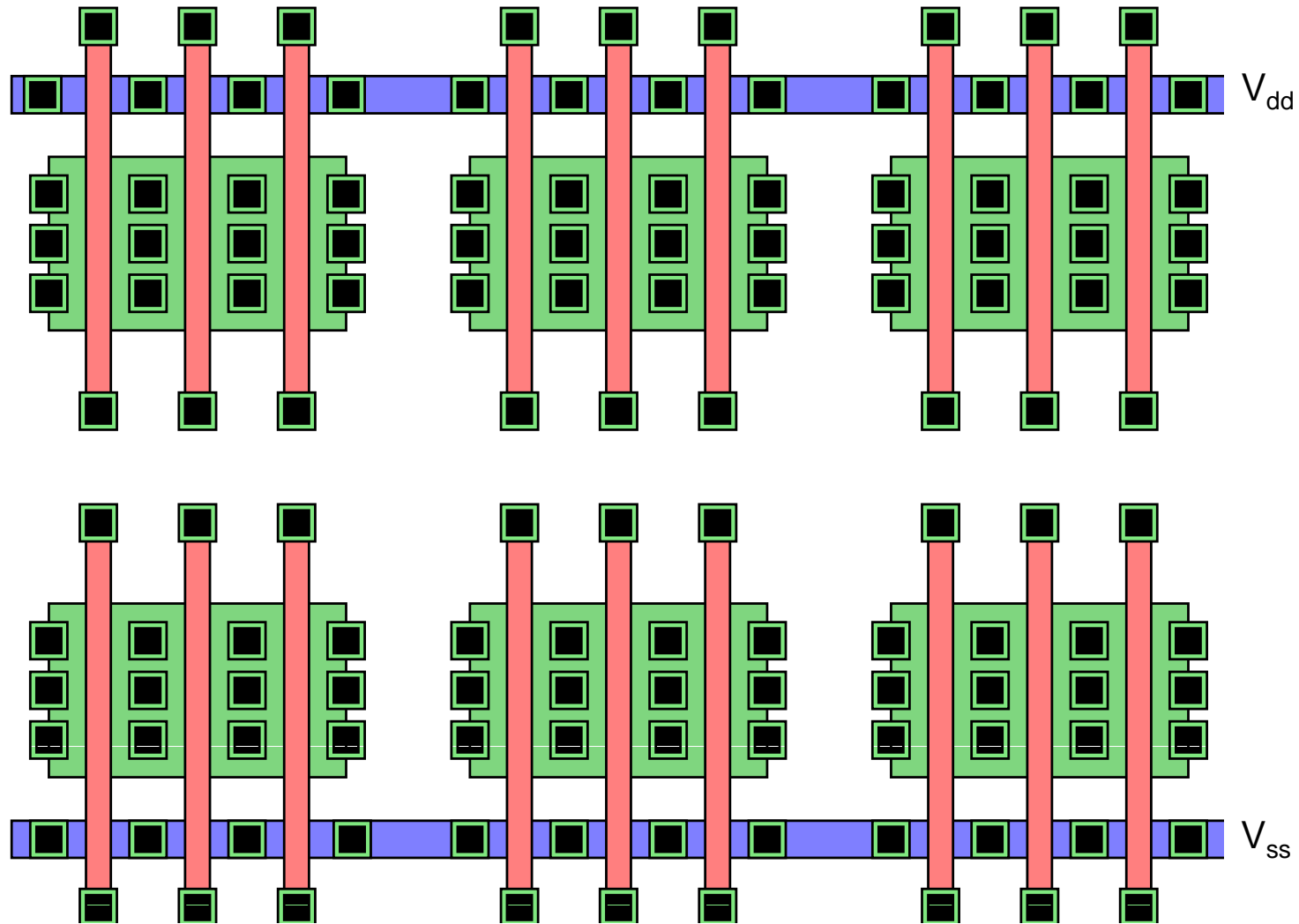
# Standard-Cell Physical Design



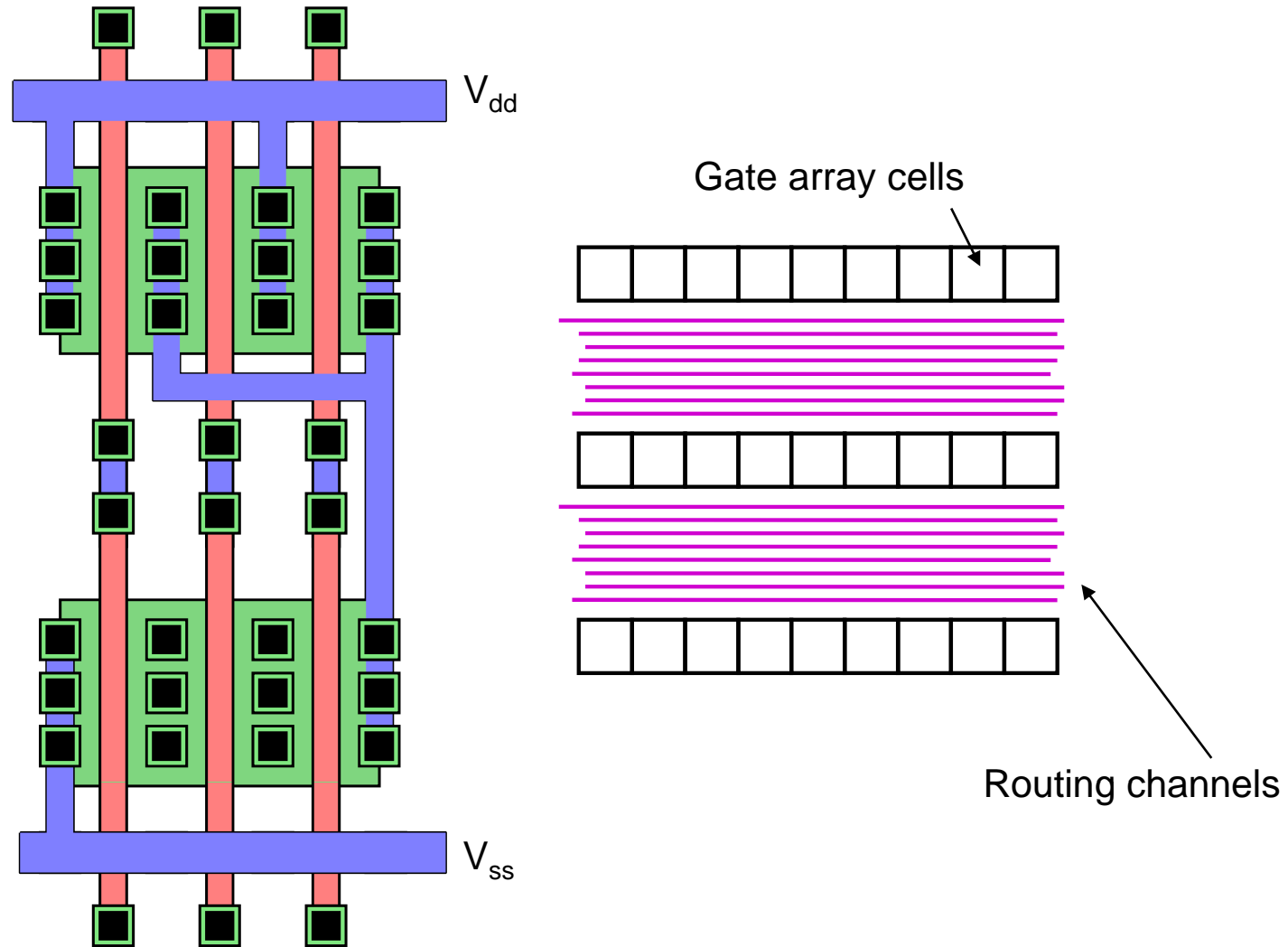
# Standard-Cell Physical Design



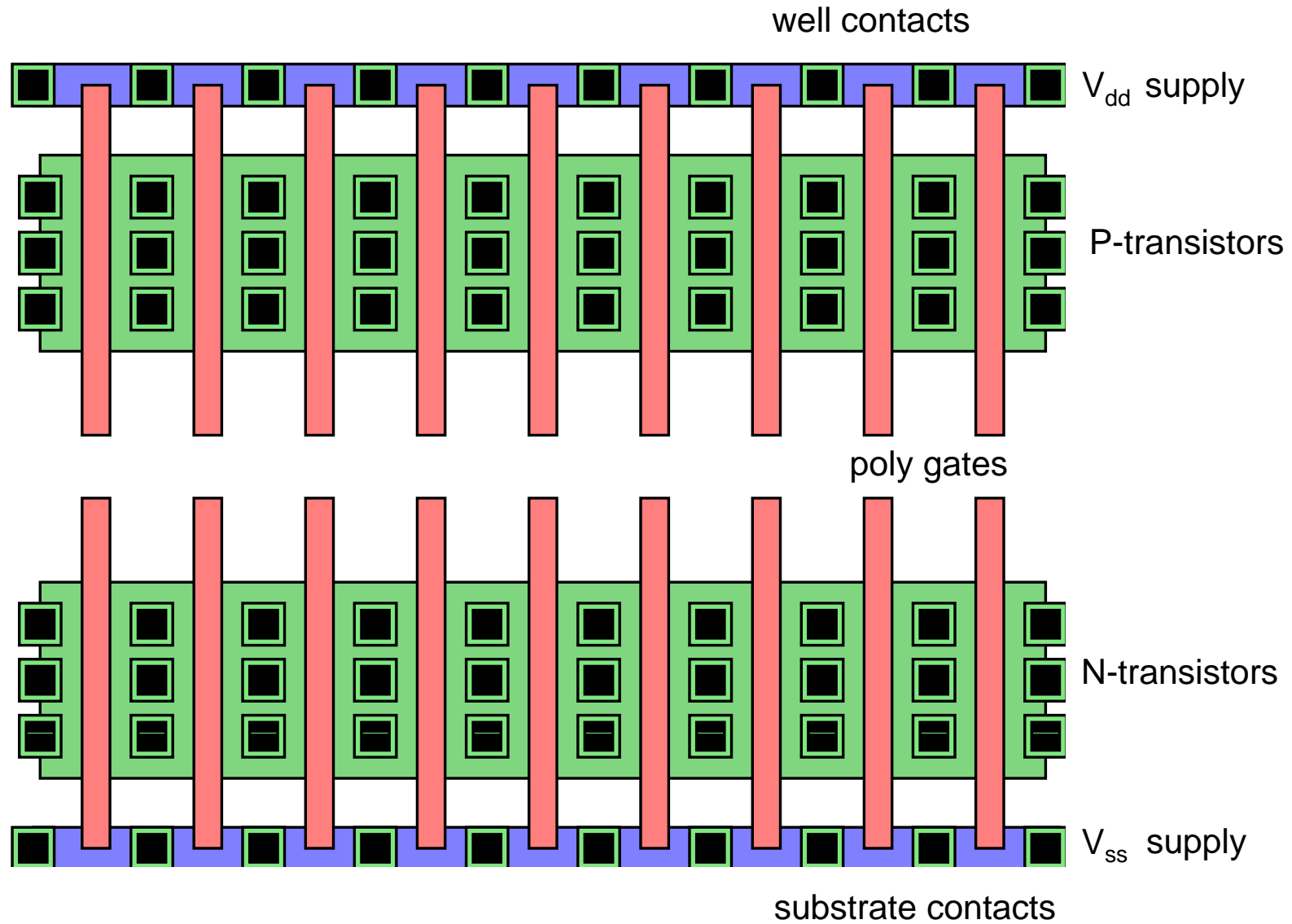
# Gate-Array Physical Design



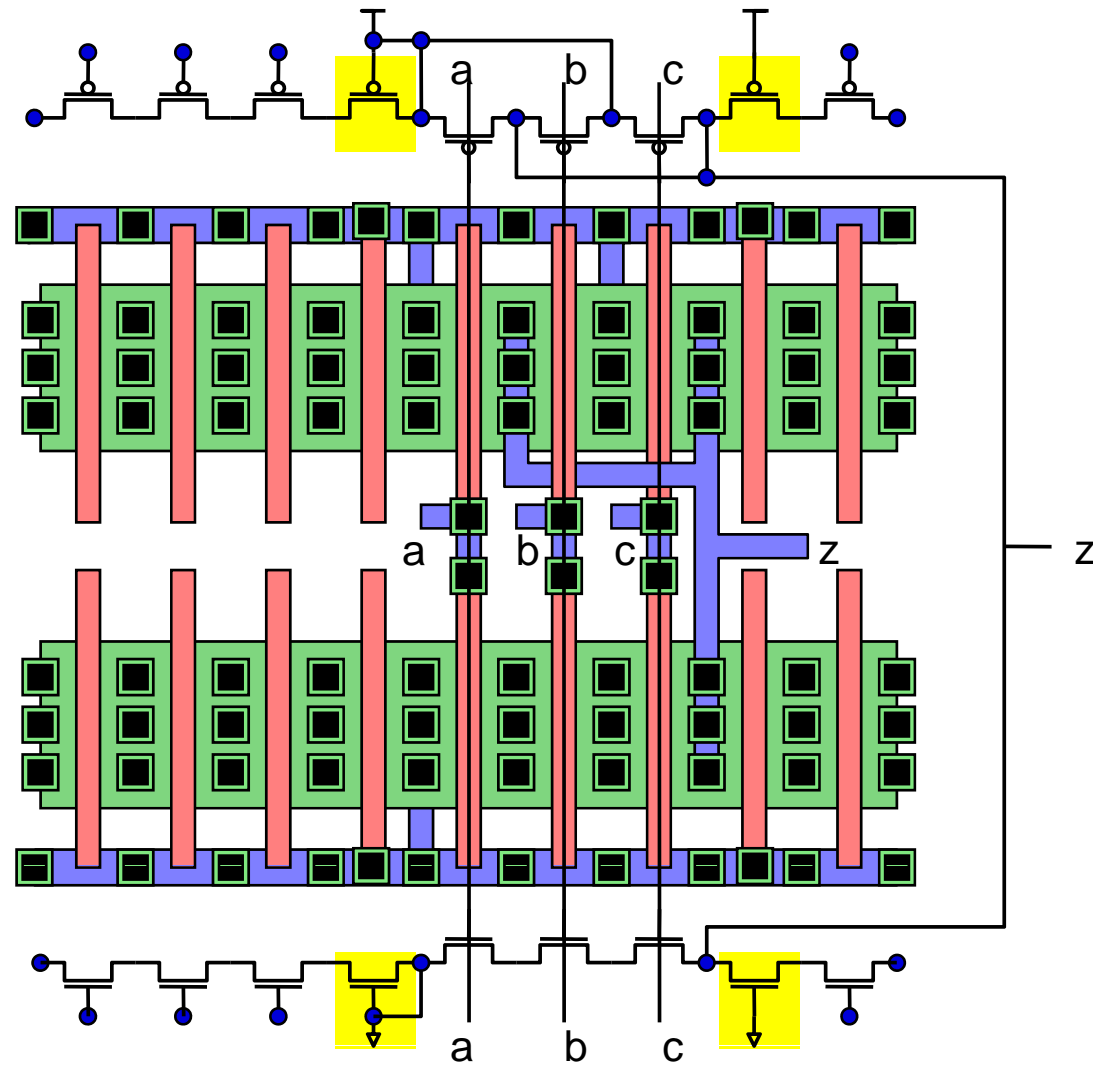
# Gate-Array Physical Design



# Sea-of-Gate Physical Design



# Sea-of-Gate Physical Design



# CMOS Layout Guidelines

- Run  $V_{DD}$  and  $V_{SS}$  in metal at the top and bottom of the cell
- Run a vertical poly line for each gate input
- Order the poly gate signals to allow the maximal connection between transistors via abutting source-drain connection
- Place n-gate segments close to  $V_{SS}$  and p-gate segments close to  $V_{DD}$
- Connection to complete the logic gate should be made in poly, metal, or, where appropriate, in diffusion

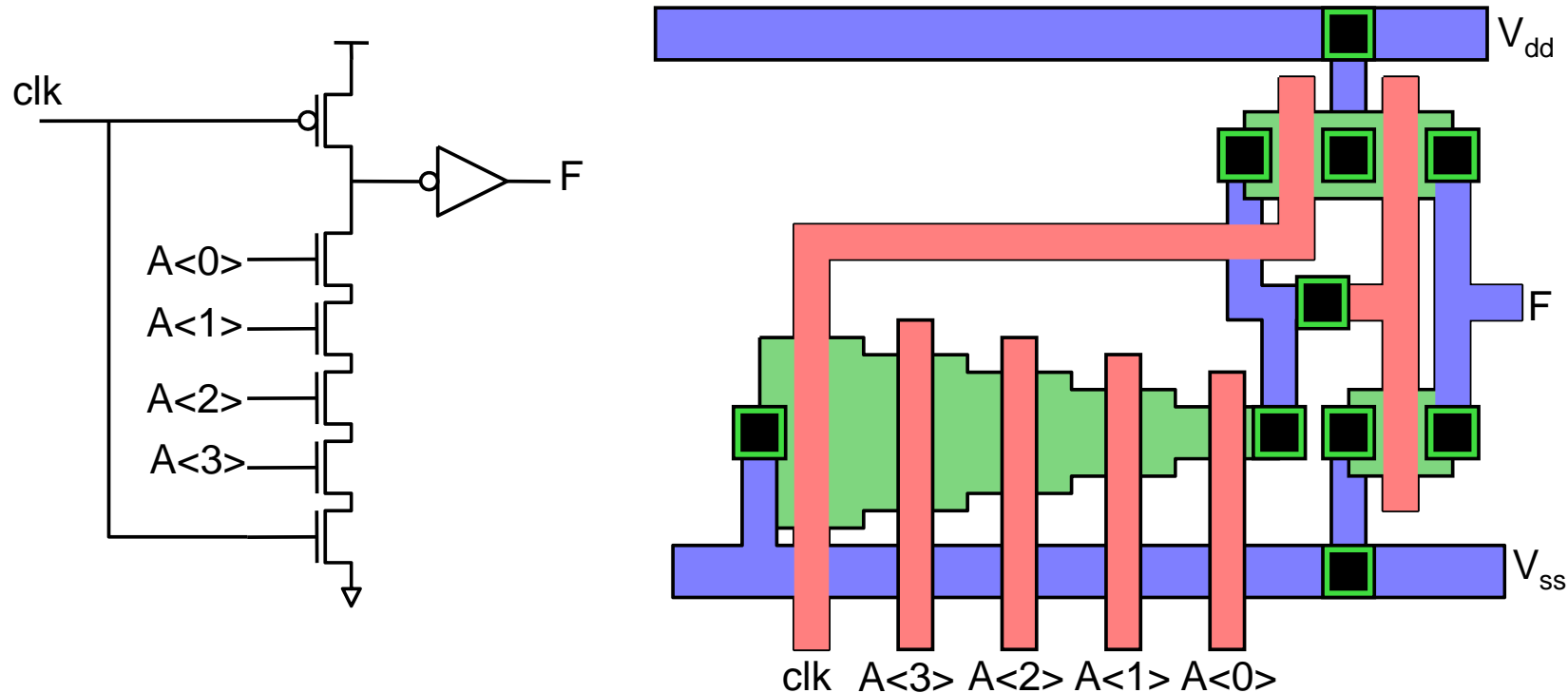


# Guidelines for Improving Density

- ❑ Better use of routing layers - routes can occur over cells
- ❑ More “merged” source-drain connections
- ❑ More usage of “white” space in sparse gates
- ❑ Use of optimum device sizes - the use of smaller devices leads to smaller layouts

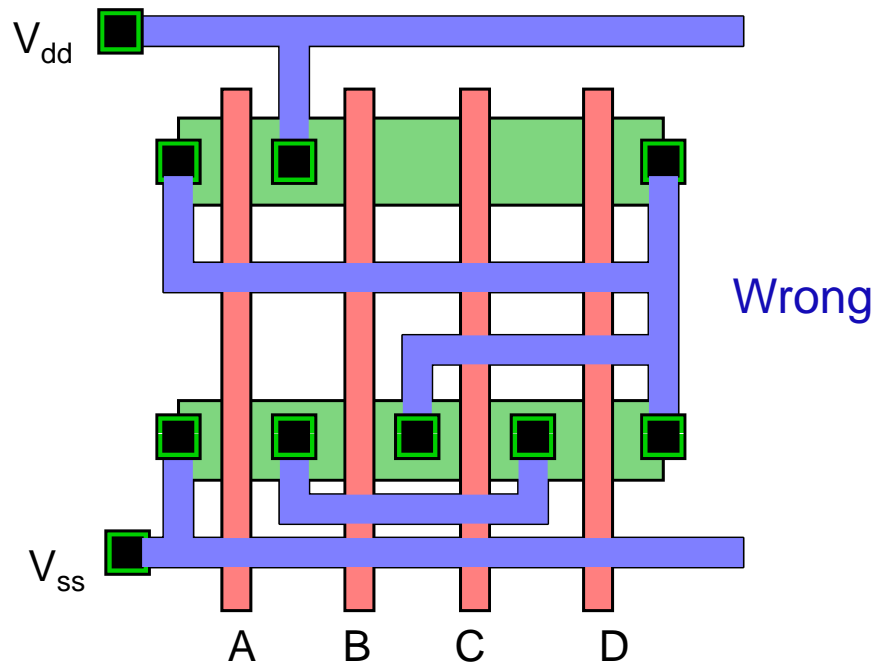
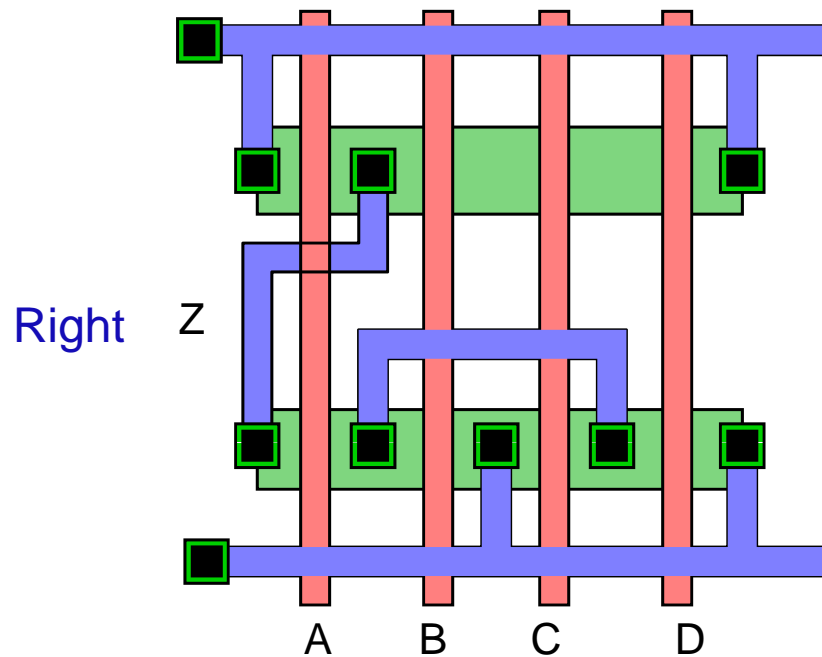
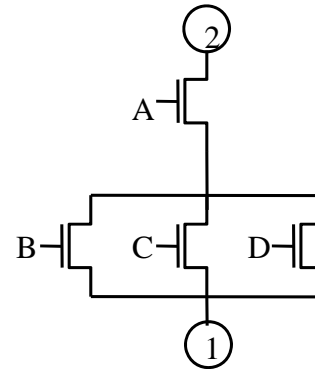
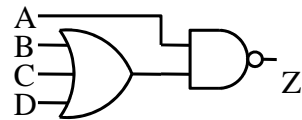
# Layout Optimization

- Vary the size of the transistor according to the position in the structure

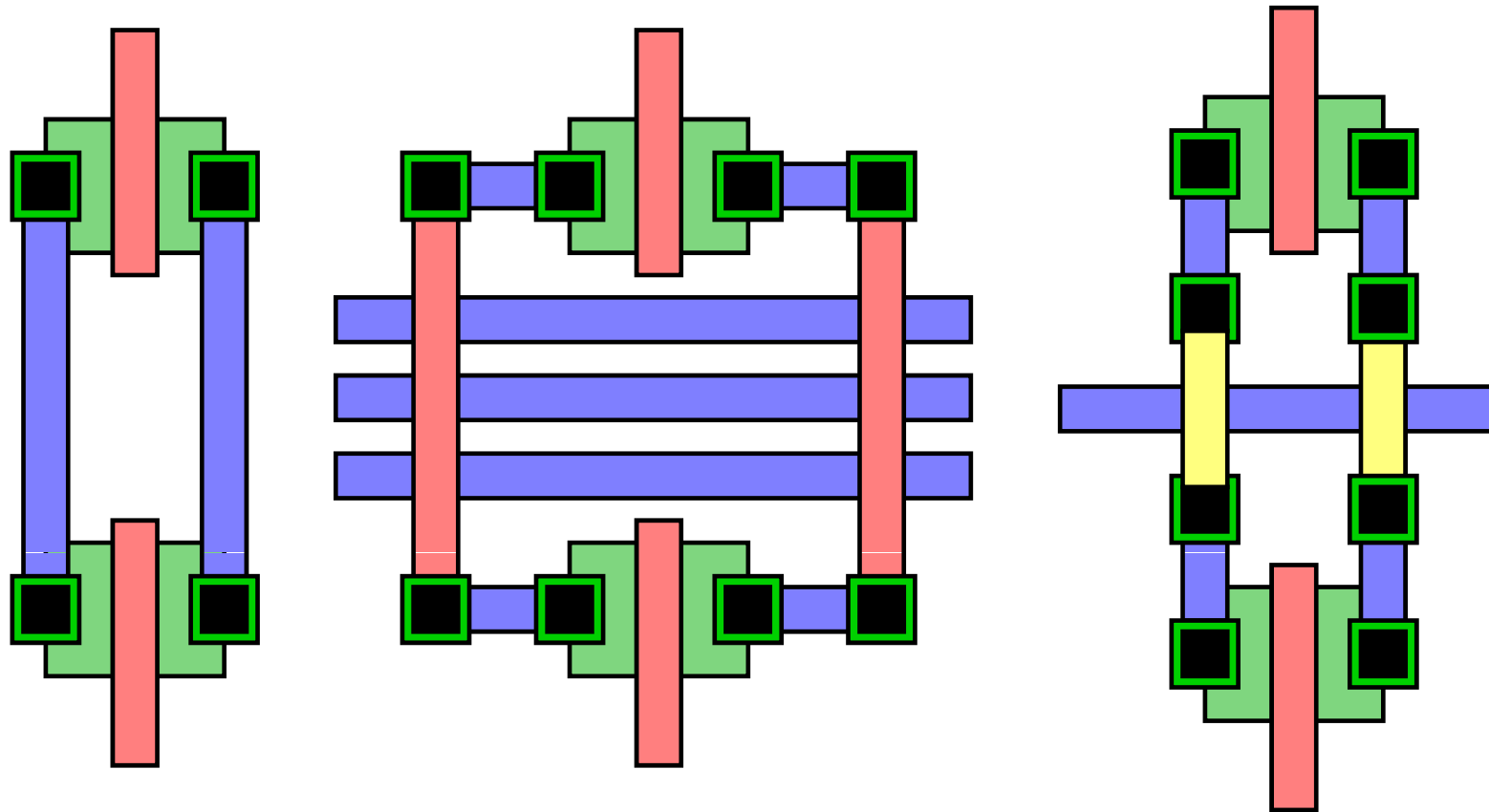


- In submicron technologies, where the source/drain capacitances are less, such that this improvement is limited

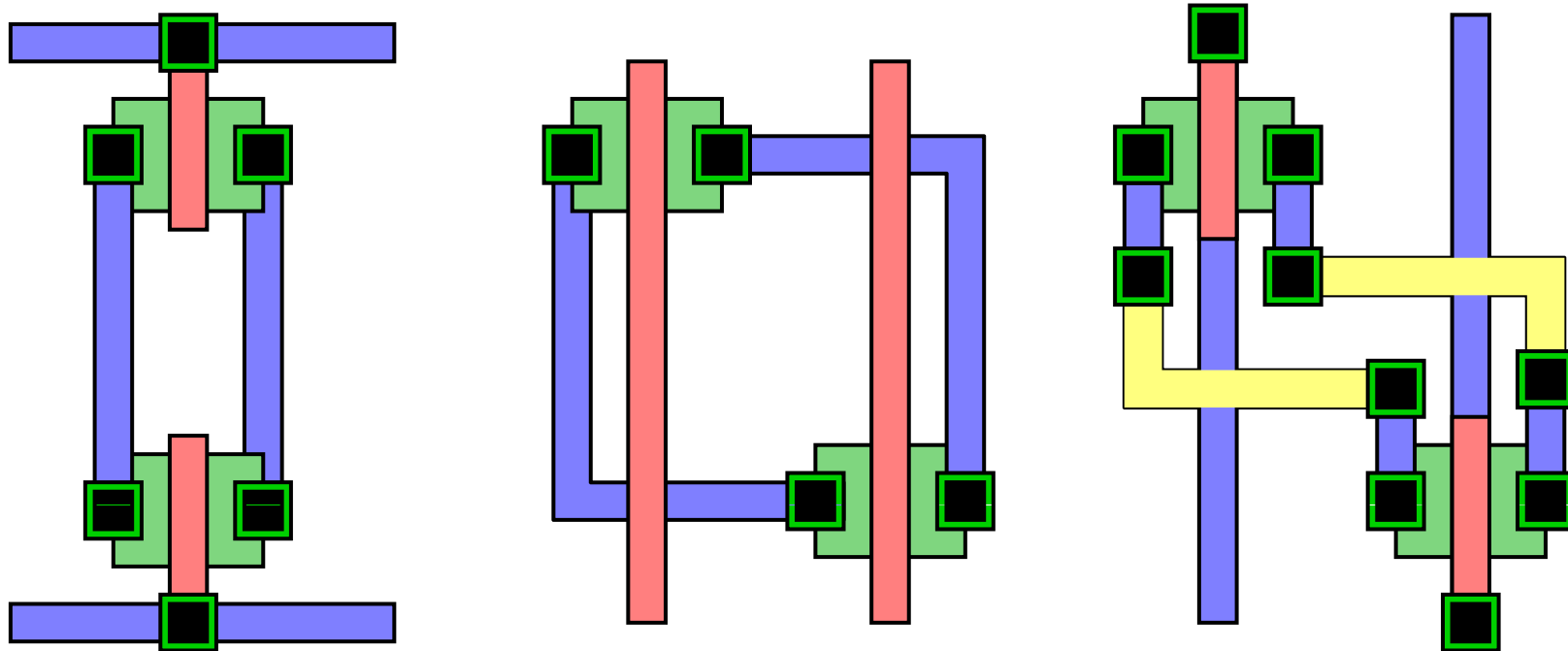
# Layout Optimization



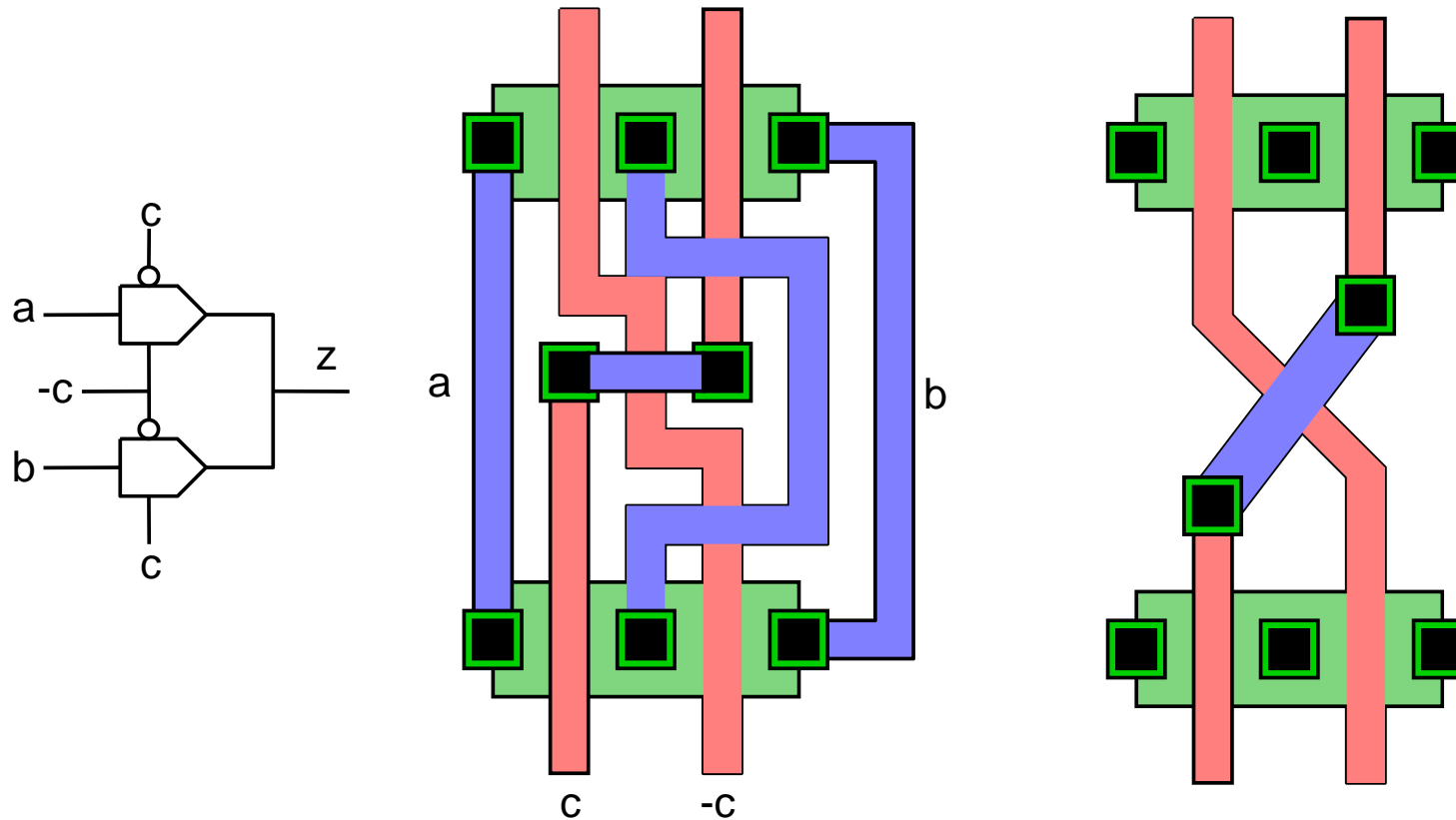
# Layouts of Transmission Gates



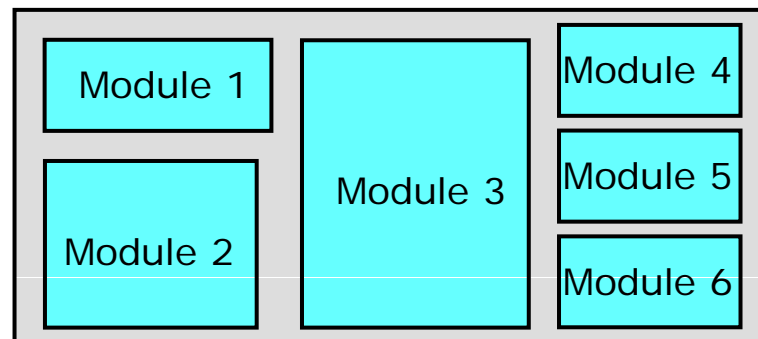
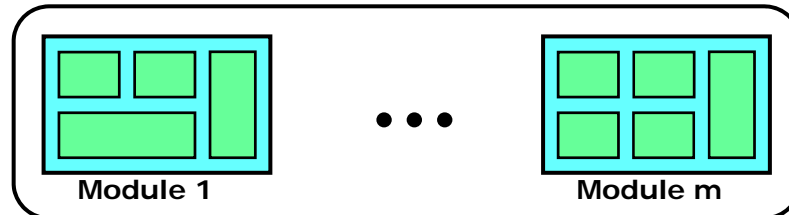
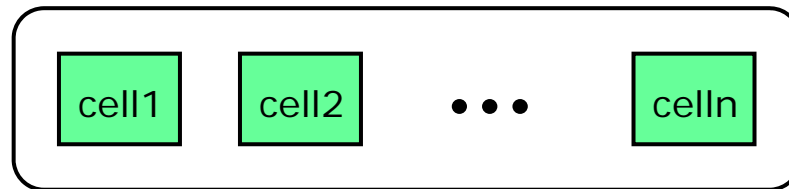
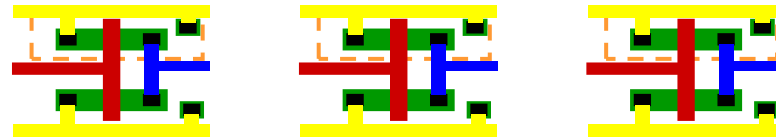
# Routing to Transmission Gates



# 2-Input Multiplexer



# Design Hierarchies



Layout level



Cell library



Subsystems



Chips

# Summary

- ❑ Basic physical design concepts have been introduced
- ❑ Cell concepts have also presented
- ❑ Layout optimization guidelines have been summarized
- ❑ Design hierarchy has been briefly introduced